

2017-03-02

FLOSFIA Inc. Raises JPY 750 Million Series B Round for Gallium Oxide Power Devices

FLOSFIA Inc. has announced that it has raised JPY 750 million from several existing and new investors including strategic ones. FLOSFIA Inc. is aiming to commercialize Corundum Structured Gallium Oxide (α -Ga₂O₃) in order to revolutionize power electronics. FLOSFIA Inc. will use this capital to develop its own production lines and commence commercial production of the world's first α -Ga₂O₃ power device in 2018.

Underwriting Companies

Miyako Capital., Ltd.

Energy & Environment Investment, Inc.

The University of Tokyo Edge Capital Co., Ltd. (UTECH)

Nissay Capital Co., Ltd.

YASKAWA Electric Corporation

Kyoto University Innovation Capital Co., Ltd

Future Venture Capital Co., Ltd.

About FLOSFIA

FLOSFIA is a startup spun out from KYOTO University, to commercialize the MIST CVD technology. The company's mission is to accelerate innovation by green and clean MISTEPITAXY® and create products that contribute to society.

President: Toshimi HITORA (CEO)

Founded in March 31, 2011

Head Quartered in Kyoto University, Katsura Campus

Business areas include Power Oxide semiconductor devices and Mist EPITAXY solution

Co-developed with Kyoto University, Advanced Electronic Materials (Fujita Lab) ,

Ritsumeikan Univ., Electrical & Electronics Eng (Araki Lab)

URL: <http://flosfia.com>

Contact Info

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